



BSS123W

#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
100V	$6.0\Omega @ V_{GS} = 10V$	170mA

### **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Small Servo Motor Control
- Power MOSFET Gate Drivers
- Switching Applications

#### **Features**

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q101) for High Reliability.
 https://www.diodes.com/quality/product-definitions/

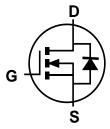
#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)

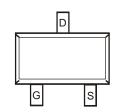




Top View



**Equivalent Circuit** 



Top View

### Ordering Information (Note 4)

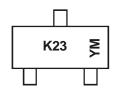
Part Number	Compliance	Case	Packaging
BSS123W-7-F	Standard	SOT323	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**



 $\begin{array}{l} \text{K23 = Product Type Marking Code} \\ \text{YM = Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: A = 2013)} \\ \text{M = Month (ex: 9 = September)} \end{array}$ 

Date Code Kev

Date Code	,													
Year	2002	2003	2004	2005	2006		2012	2013	2014	2015	2016	2017	2018	2019
Code	N	Р	R	S	Т		Z	Α	В	С	D	Е	F	G
Month	Jan	Feb	Ma	ar	Apr	May	Jun	Jul	Aug	Se	р (	Oct	Nov	Dec
Code	1	2	3		4	5	6	7	8	9		0	N	D

# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characte	ristic	Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	100	V
Drain-Gate Voltage $R_{GS} \le 20K\Omega$		$V_{DGR}$	100	V
Gate-Source Voltage Continuous		V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Continuous Pulsed	I <sub>D</sub> I <sub>DM</sub>	170 680	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	$BV_{DSS}$	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current		_	_	1.0 10	μA nA	$V_{DS} = 100V, V_{GS} = 0V$ $V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage, Forward	I <sub>GSSF</sub>	_	_	50	nA	$V_{GS} = 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	1.4	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		_	6.0 10	Ω	$V_{GS} = 10V, I_D = 0.17A$ $V_{GS} = 4.5V, I_D = 0.17A$
Forward Transconductance	g <sub>F</sub> s	80	370	_	mS	$V_{DS} = 10V$ , $I_D = 0.17A$ , $f = 1.0KHz$
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	_	0.84	1.3	V	$V_{GS} = 0V, I_{S} = 0.34A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	Ciss	_	29	60	pF	
Output Capacitance	Coss	_	10	15	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2	6	pF	
SWITCHING CHARACTERISTICS(Note 7)						
Turn-On Rise Time	t <sub>r</sub>	_	_	8	ns	
Turn-Off Fall Time		_	_	16	ns	$V_{DD} = 30V, I_D = 0.28A,$
Turn-On Delay Time	t <sub>D(ON)</sub>	_	_	8	ns	$R_{GEN} = 6.0\Omega$ , $V_{GS} = 10V$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_		13	ns	

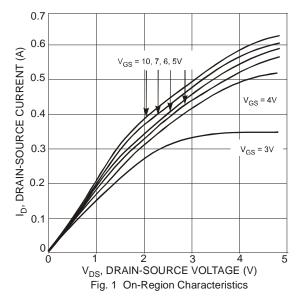
Notes: 5. Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com.

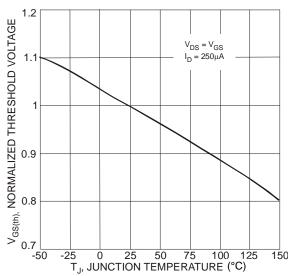
6. Short duration pulse test used to minimize self-heating effect.

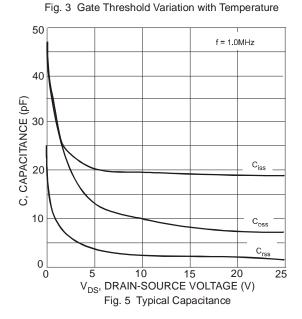
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<sup>7.</sup> Guaranteed by design. Not subject to production testing.









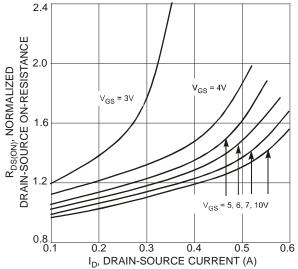


Fig. 2 On-Resistance Variation with Gate Voltage and Drain-Source Current

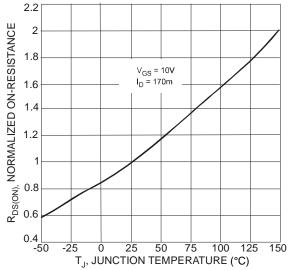


Fig. 4 On-Resistance Variation with Temperature

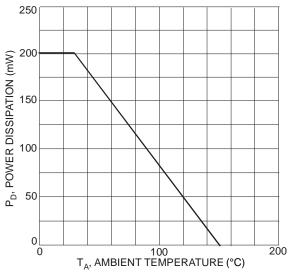
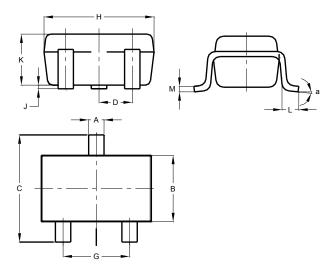


Fig. 6 Power Derating Curve, Total Package



# **Package Outline Dimensions**

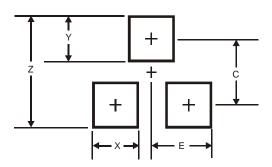
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	0.	.650 BS	С				
F	0.375	0.475	0.425				
G	1.20	1.40	1.30				
Н	1.80	2.20	2.15				
J	0.00	0.10	0.05				
K	0.90	1.00	0.95				
L	0.25	0.40	0.30				
M	0.10	0.18	0.11				
а	8°C						
All Dimensions in mm							

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0



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